



General Description

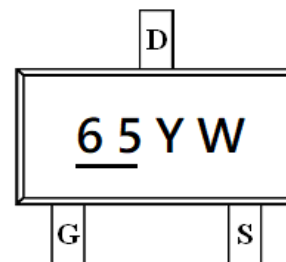
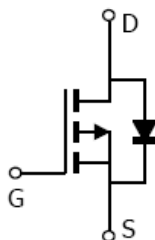
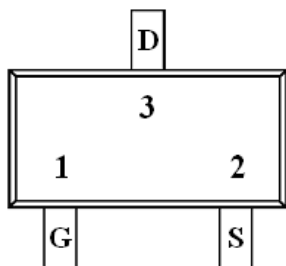
AFP2365A, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- $I_D = -6.0A, R_{DS(ON)} = 32m\Omega @ V_{GS} = 4.5V$
- $I_D = -4.0A, R_{DS(ON)} = 40m\Omega @ V_{GS} = 2.5V$
- $I_D = -2.0A, R_{DS(ON)} = 55m\Omega @ V_{GS} = 1.8V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

Pin Description (SOT-23)



Application

- Portable Equipment
- Battery Powered System
- Net Working System

Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP2365AS23RG	65YW	SOT-23	Tape & Reel	3000 EA

- ※ 65 parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFP2365AS23RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate -Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (T _J =150°C)	I _D	T _C =25°C T _A =25°C	-6.0
		T _C =75°C T _A =75°C	-4.2
Pulsed Drain Current	I _{DM}	-20	A
Continuous Source Current (Diode Conduction)	I _S	-1.4	A
Power Dissipation	P _D	T _C =25°C T _A =25°C	1.7
		T _C =75°C T _A =75°C	1.1
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

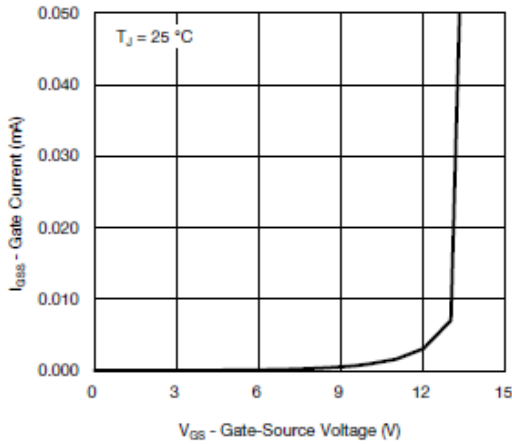
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

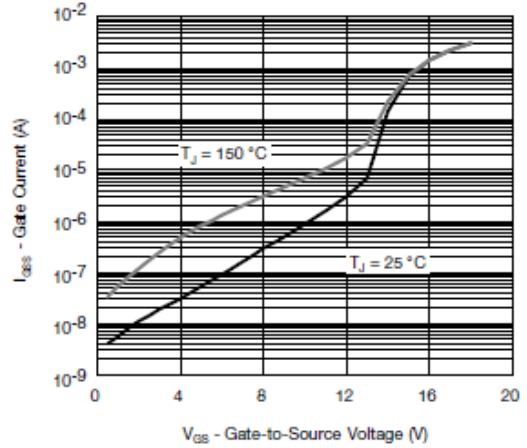
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-0.3	-0.5	-1.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-16V, V _{GS} =0V			-1	uA
		V _{DS} =-16V, V _{GS} =0V T _J =85°C			-10	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ -5V, V _{GS} =-4.5V	-15			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-6.0A		25	32	mΩ
		V _{GS} =-2.5V, I _D =-4.0A		32	40	
		V _{GS} =-1.8V, I _D =-2.0A		42	55	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-4.0A		20		S
Diode Forward Voltage	V _{SD}	I _S =-3.6A, V _{GS} =0V		-0.85	-1.3	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-10V, V _{GS} =-4.5V I _D ≡-4.5A		13	21	nC
Gate-Source Charge	Q _{gs}			2		
Gate-Drain Charge	Q _{gd}			3		
Input Capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0V f=1MHz		1250		pF
Output Capacitance	C _{oss}			235		
Reverse Transfer Capacitance	C _{rss}			200		
Turn-On Time	t _{d(on)}	V _{DD} =-10V, R _L =2.8Ω I _D ≡-3.6A, V _{GEN} =-4.5V R _G =1Ω		20	40	us
	t _r			20	40	
Turn-Off Time	t _{d(off)}			50	100	
	t _f			15	30	



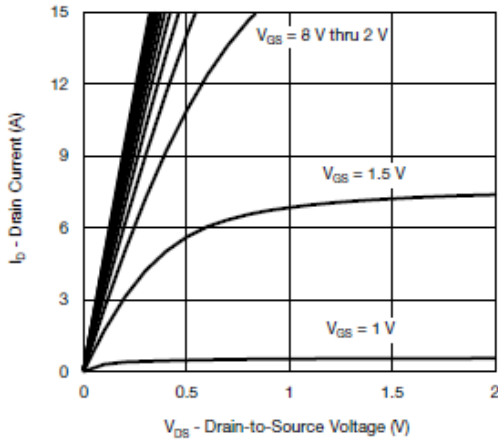
Typical Characteristics



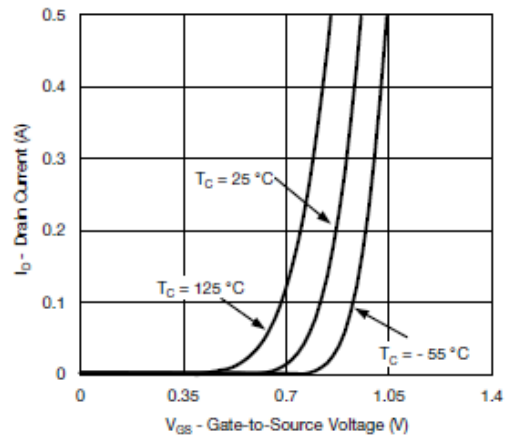
Gate Current vs. Gate-Source Voltage



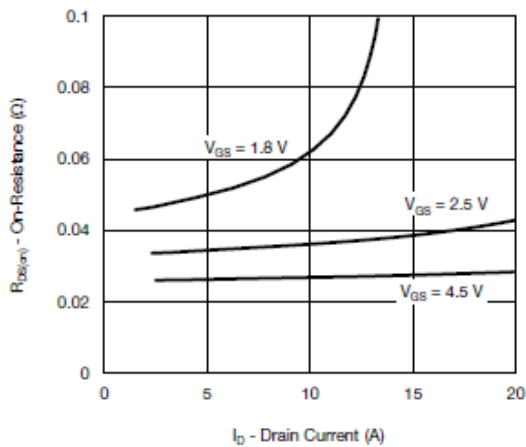
Gate Current vs. Gate-Source Voltage



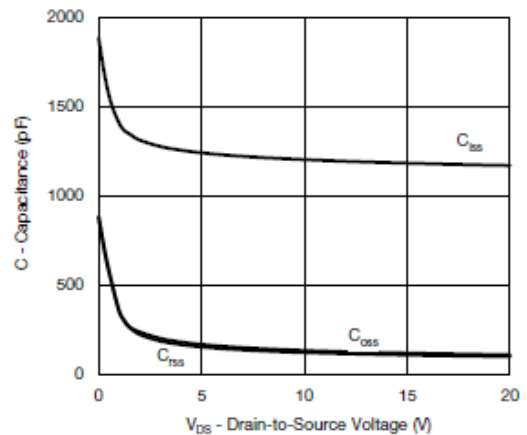
Output Characteristics



Transfer Characteristics



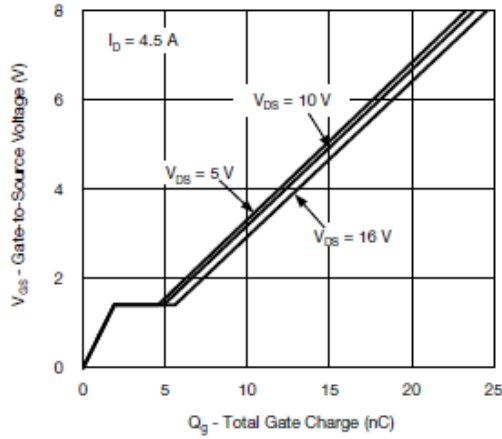
On-Resistance vs. Drain Current



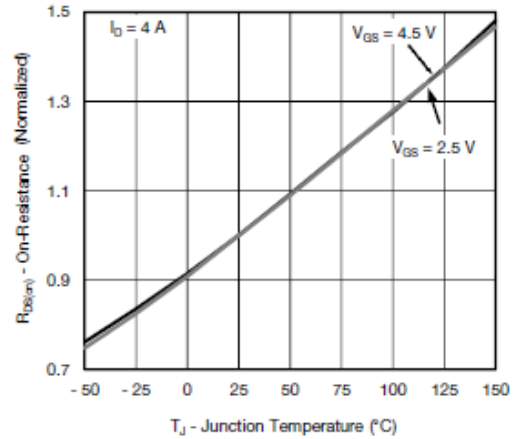
Capacitance



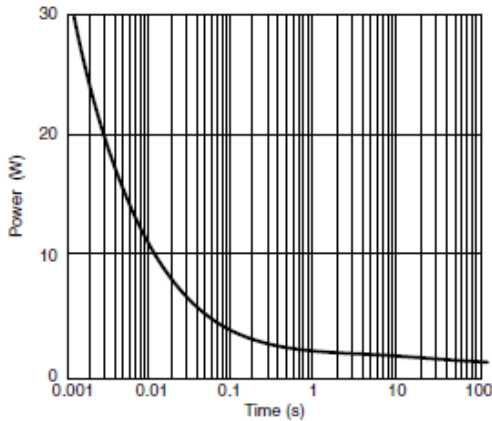
Typical Characteristics



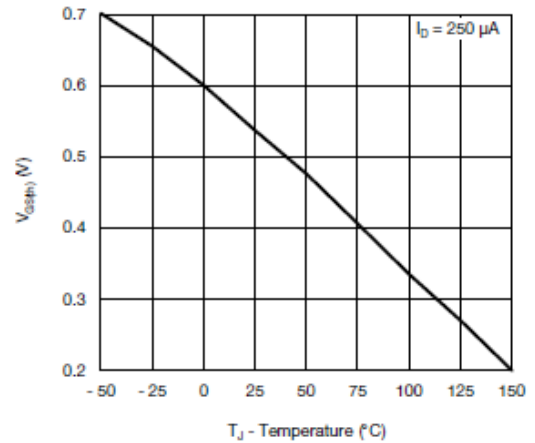
Gate Charge



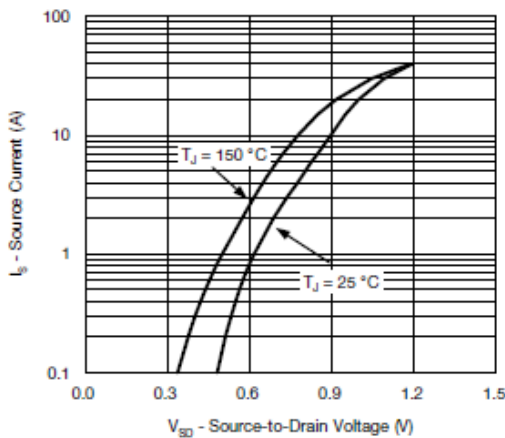
On-Resistance vs. Junction Temperature



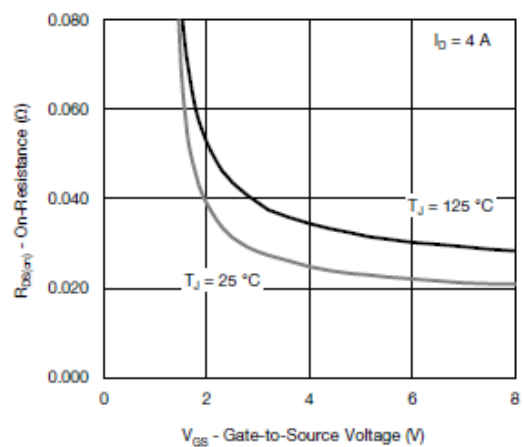
Single Pulse Power, Junction-to-Ambient



Threshold Voltage



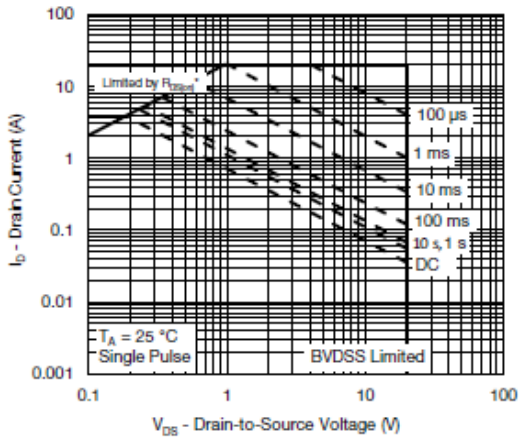
Source-Drain Diode Forward Voltage



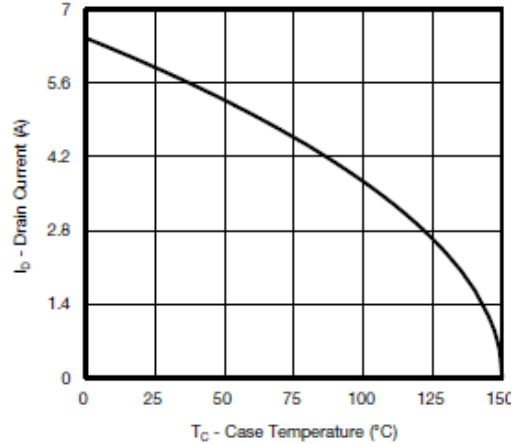
On-Resistance vs. Gate-to-Source Voltage



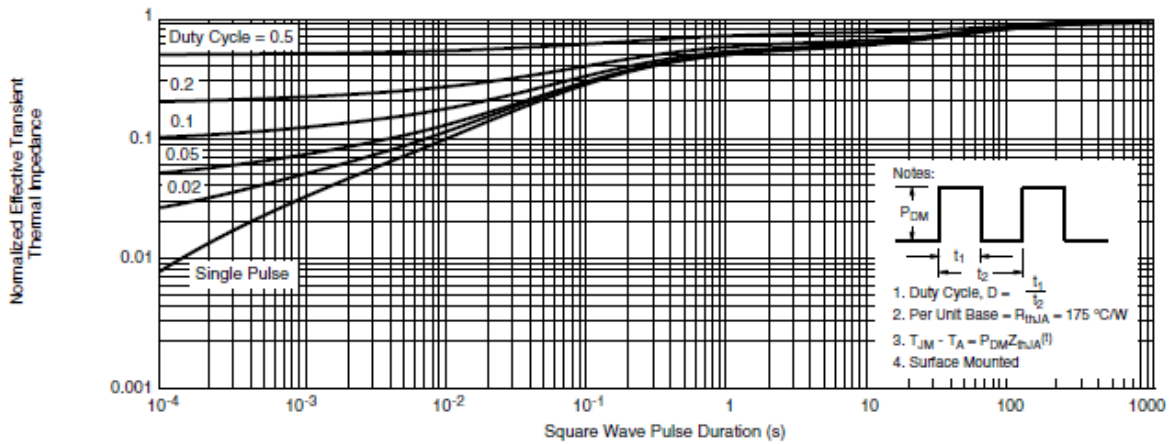
Typical Characteristics



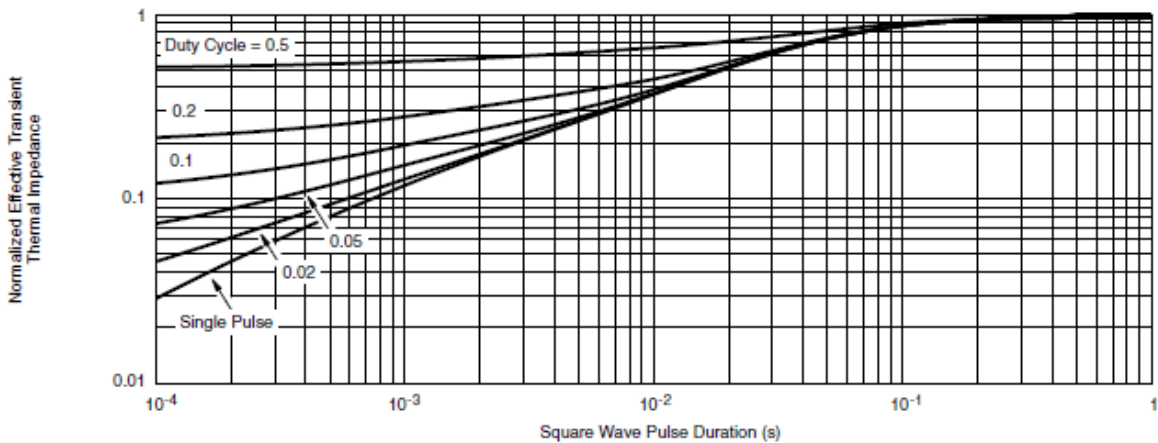
V_{DS} - Drain-to-Source Voltage (V)
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient



Current Derating*



Normalized Thermal Transient Impedance, Junction-to-Ambient

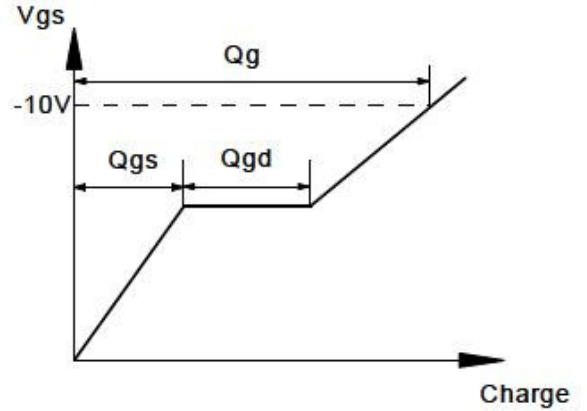
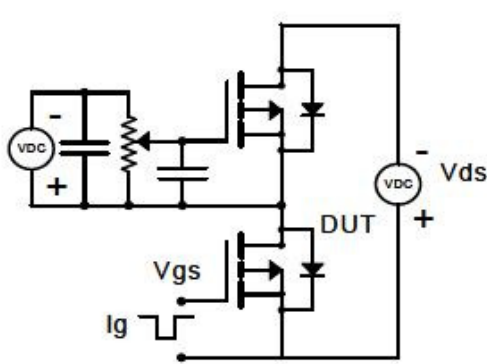


Normalized Thermal Transient Impedance, Junction-to-Foot

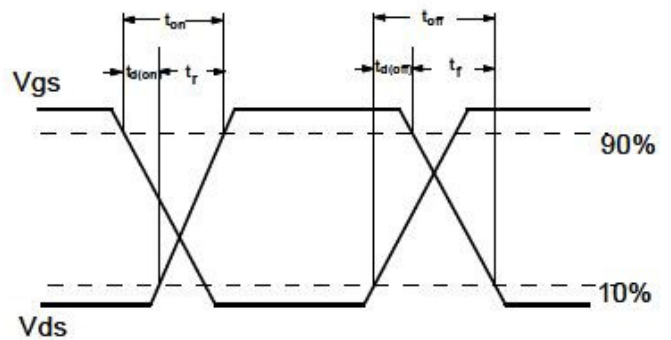
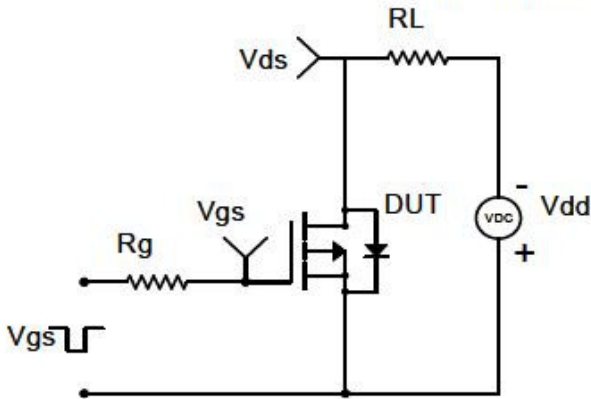


Typical Characteristics

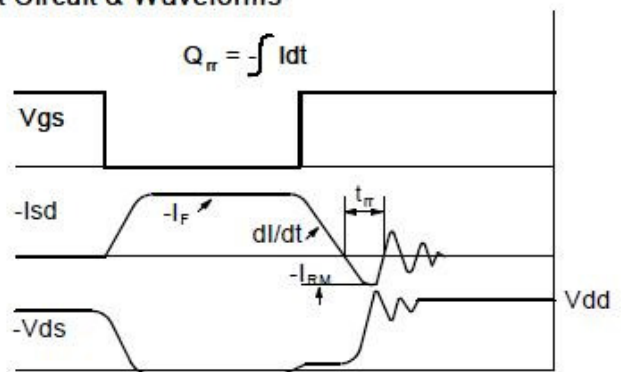
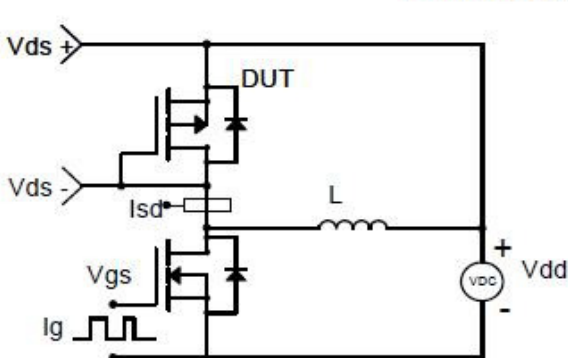
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

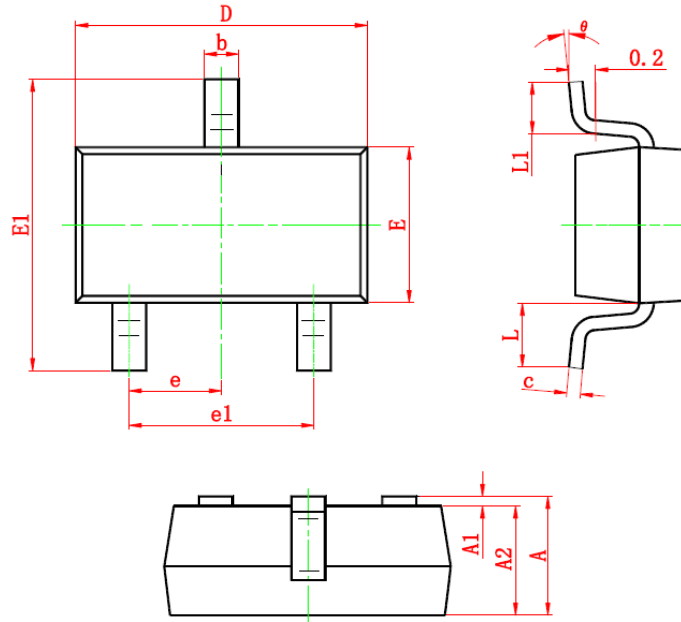


Diode Recovery Test Circuit & Waveforms





Package Information (SOT-23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

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**Alfa-MOS
Technology**

AFP2365A
20V P-Channel
Enhancement Mode MOSFET
